

Erratum: "Electronic transport and microstructure in MoSi₂ thin films" [J. Mater. Res. 1, 493 (1986)]

T. L. Martin^{a)} and J. E. Mahan

Department of Electrical Engineering and Condensed Matter Sciences Laboratory, Colorado State University, Fort Collins, Colorado 80523

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When this article was published in the May/June 1986 issue of *Journal of Materials Research*, a line was inadvertently omitted from the introduction at the final correction phase. The third paragraph on page 493 of this article should read:

"In 1956, it was predicted from energy band calculations that MoSi₂ is a metallic conductor.²⁰ The states

near the Fermi energy were said to be due to a mixing of silicon 3s and 3p states with molybdenum 4s and 5d states. The partial filling of some bands leads to metallic conduction. It was suggested then that the electron effective mass is highly anisotropic."

^{a)} Present address: Intel Corporation, Chandler, Arizona.